

NPN Silicon Transistor

BUT11AF



TO-220 Fullpack, 3-Lead
CASE 221AT

High Voltage Power Switching Applications

MAXIMUM RATINGS (T_C = 25 °C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	1000	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	5	A
I _{CP}	*Collector Current (Pulse)	10	A
I _B	Base Current (DC)	2	A
I _{BP}	*Base Current (Pulse)	4	A
P _C	Collector Dissipation (T _C = 25°C)	40	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65~150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

MARKING DIAGRAM

BUT11A F AYWWZZ

BUT11AF = Specific Device Code
A = Site Code
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

ORDERING INFORMATION

Device	Package	Shipping
BUT11AFTU	TO-220 Fullpack (Pb-Free)	1000 Units / Tube

THERMAL CHARACTERISTICS (T_C = 25 °C, unless otherwise noted)

Symbol	Parameter	Max	Unit
R _{θJC}	Thermal Resistance, Junction to Case	3.125	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO(sus)}	*Collector-Emitter Sustaining Voltage	I _C = 100 mA, I _B = 0	450	-	-	V
I _{CES}	Collector Cut-off Current	V _{CE} = 1000 V, V _{BE} = 0	-	-	1	mA
I _{EBO}	Emitter Cut-off Current	V _{BE} = 9 V, I _C = 0	-	-	10	mA
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2.5 A, I _B = 0.5 A	-	-	1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 2.5 A, I _B = 0.5 A	-	-	1.3	V
t _{ON}	Turn On Time	V _{CC} = 250 V, I _C = 2.5 A, I _{B1} = -I _{B2} = 0.5 A, R _L = 100 Ω	-	-	1	μs
t _{STG}	Storage Time		-	-	4	μs
t _F	Fall Time		-	-	0.8	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*Pulsed: pulsed duration = 300 μs, duty cycle = 1.5%

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TYPICAL CHARACTERISTICS

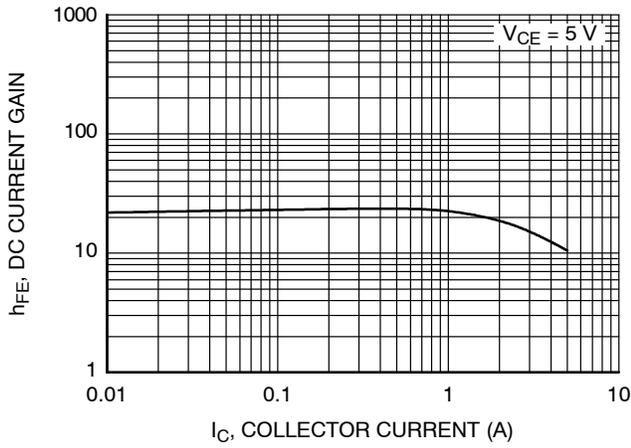


Figure 1. DC Current Gain

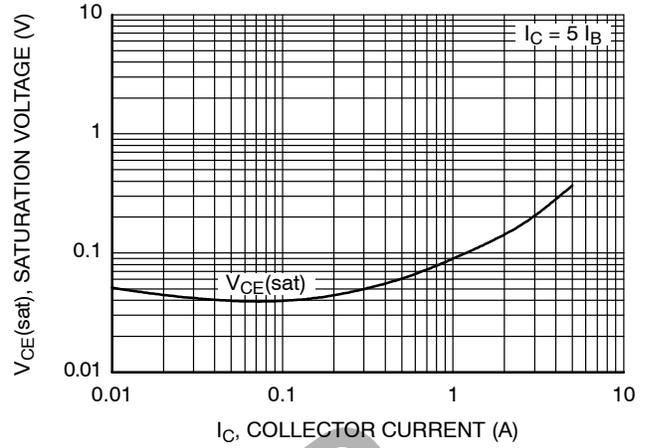


Figure 2. Collector-Emitter Saturation Voltage

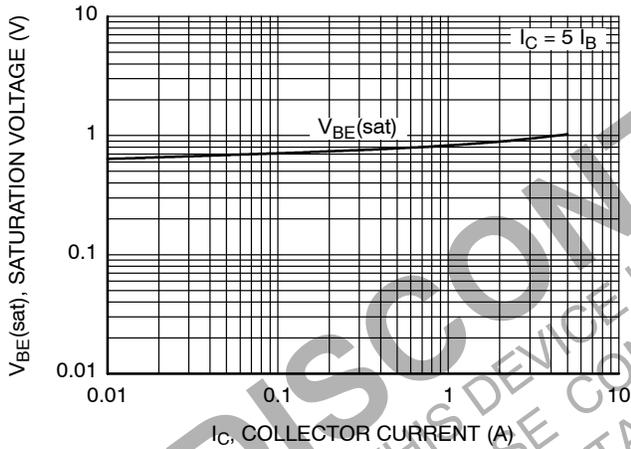


Figure 3. Base-Emitter Saturation Voltage

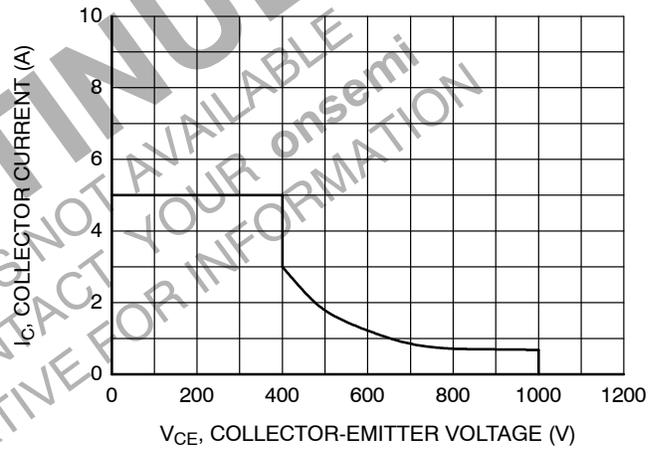


Figure 4. Reverse Biased Safe Operating Area

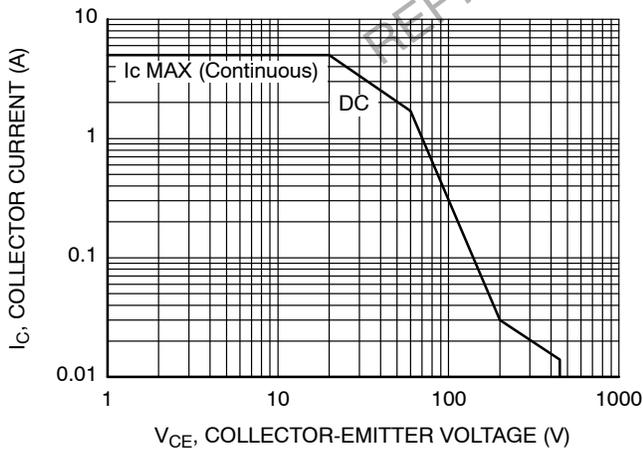


Figure 5. Safe Operating Area

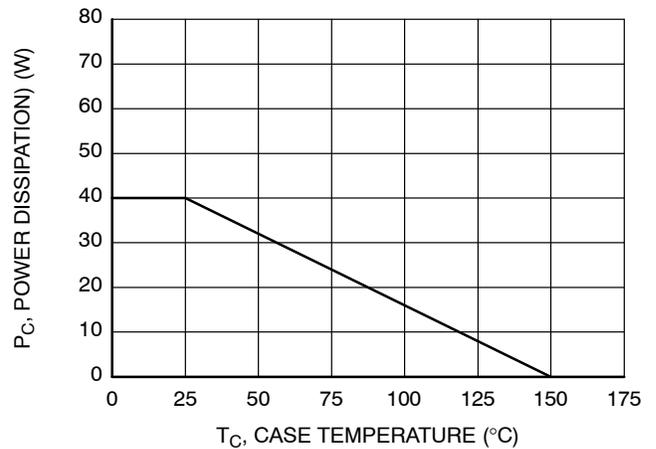


Figure 6. Power Derating

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REVISION HISTORY

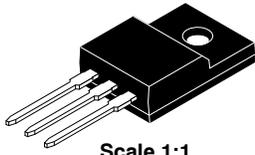
Revision	Description of Changes	Date
2	Document Discontinued.	11/10/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

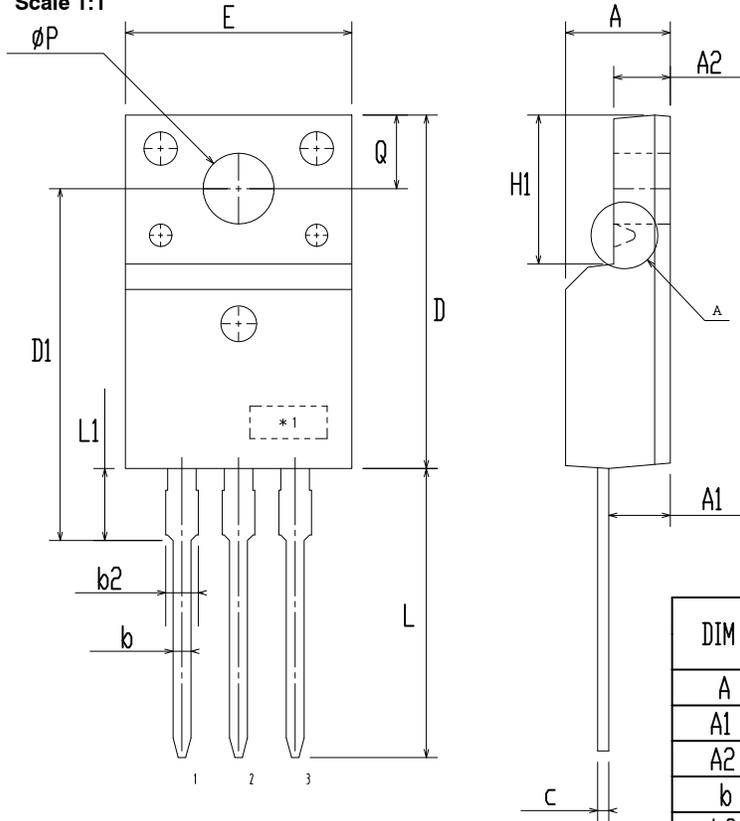
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THIS DEVICE IS NOT AVAILABLE
PLEASE CONTACT YOUR onsemi
REPRESENTATIVE FOR INFORMATION

TO-220 Fullpack, 3-Lead / TO-220F-3SG
CASE 221AT
ISSUE B

DATE 19 JAN 2021



Scale 1:1



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.56	2.76	2.96
A2	2.34	2.54	2.74
b	0.70	0.80	0.90
b2	~	~	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.60	15.80	16.00
E	9.96	10.16	10.36
e	2.34	2.54	2.74
F	~	0.84	~
H1	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
∅ P	2.98	3.18	3.38
∅ P1	~	1.00	~
Q	3.20	3.30	3.40

NOTES:

- A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCTIONS.
- C. OPTION 1 - WITH SUPPORT PIN HOLE
- OPTION 2 - NO SUPPORT PIN HOLE

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